

### General Description

The WSF45P10 is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the small power switching and load switch applications.

The WSF45P10 meet the RoHS and Green Product requirement with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

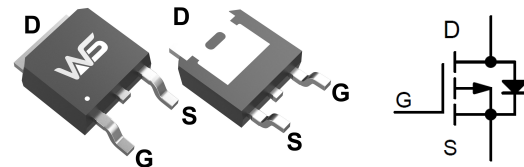
### Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$
-100V	44m $\Omega$	-40A

### Applications

- Inverters

### TO-252 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
<b>Common Ratings</b> ( $T_C=25^\circ\text{C}$ Unless Otherwise Noted)			
$V_{DSS}$	Drain-Source Voltage	-100	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$T_J$	Maximum Junction Temperature	175	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
$I_S$	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ -40	A
<b>Mounted on Large Heat Sink</b>			
$I_{DM}$	Pulsed Drain Current *	-120**	A
$I_D$	Continuous Drain Current	$T_C=25^\circ\text{C}$ -40	A
		$T_C=100^\circ\text{C}$ -26	
$P_D$	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 136	W
		$T_C=100^\circ\text{C}$ 68	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.1	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	
<b>Avalanche Ratings</b>			
$E_{AS}$	Avalanche Energy, Single Pulsed	$L=0.5\text{mH}$ 308***	mJ

Note : \* Repetitive rating ; pulse width limited by junction temperatur

\*\* Drain current is limited by junction temperature

\*\*\*  $V_D=-80\text{V}$

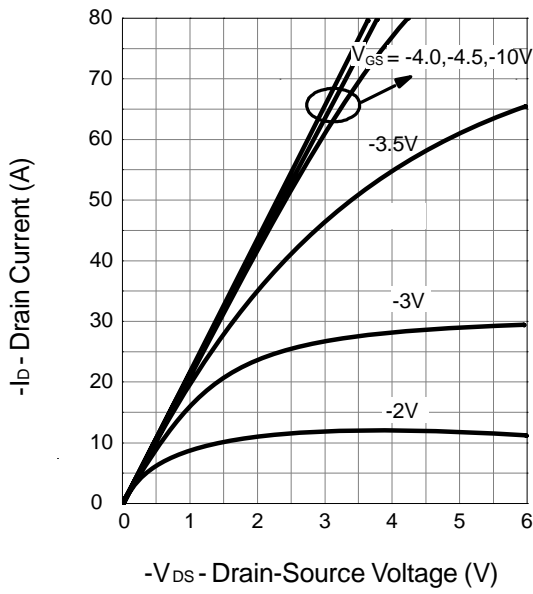
**Electrical Characteristics** ( $T_C=25^\circ\text{C}$  Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=-250\mu A$	-100	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-100V, V_{GS}=0V$ $T_J=85^\circ\text{C}$	-	-	-1	$\mu A$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-1	-2	-3	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
$R_{DS(ON)}^*$	Drain-Source On-state Resistance	$V_{GS}=-10V, I_{DS}=-20A$	-	44	55	$m\Omega$
$R_{DS(ON)}^*$	Drain-Source On-state Resistance	$V_{GS}=-4.5V, I_{DS}=-20A$	-	47	58.5	$m\Omega$
<b>Diode Characteristics</b>						
$V_{SD}^*$	Diode Forward Voltage	$I_{SD}=-20A, V_{GS}=0V$	-	-0.8	-1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=-20A, dI_{SD}/dt=-100A/\mu s$	-	70	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	90	-	nC
<b>Dynamic Characteristics</b>						
$R_G$	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	-	2	-	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=-20V,$ Frequency=1.0MHz	-	5720	-	pF
$C_{oss}$	Output Capacitance		-	790	-	
$C_{riss}$	Reverse Transfer Capacitance		-	450	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=-50V, R_G=6\Omega,$ $I_{DS}=-20A, V_{GS}=-10V,$	-	30	-	ns
$T_r$	Turn-on Rise Time		-	79	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	82	-	
$T_f$	Turn-off Fall Time		-	69	-	
<b>Gate Charge Characteristics</b>						
$Q_g$	Total Gate Charge	$V_{DS}=-80V, V_{GS}=-10V,$ $I_{DS}=-20A$	-	125	-	nC
$Q_{gs}$	Gate-Source Charge		-	21	-	
$Q_{gd}$	Gate-Drain Charge		-	45	-	

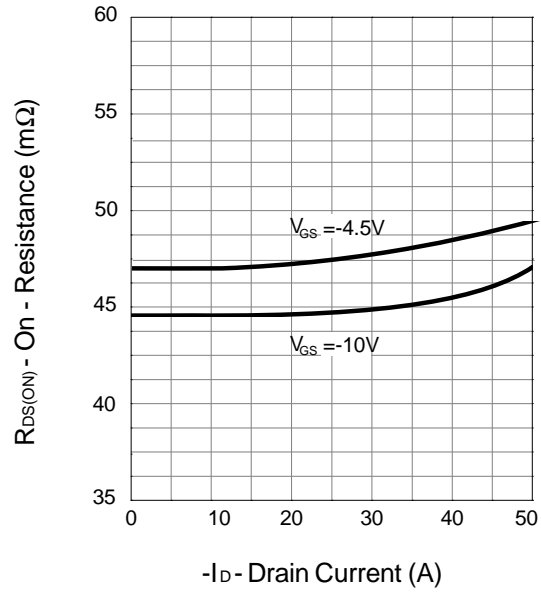
Note \* : Pulse test ; pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

**Typical Characteristics**

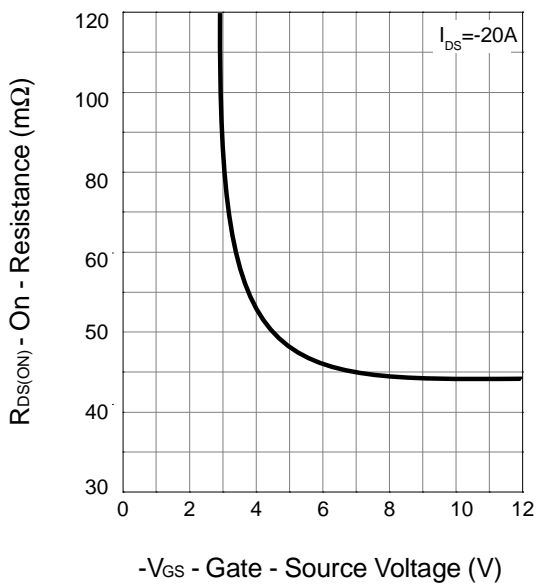
**Output Characteristics**



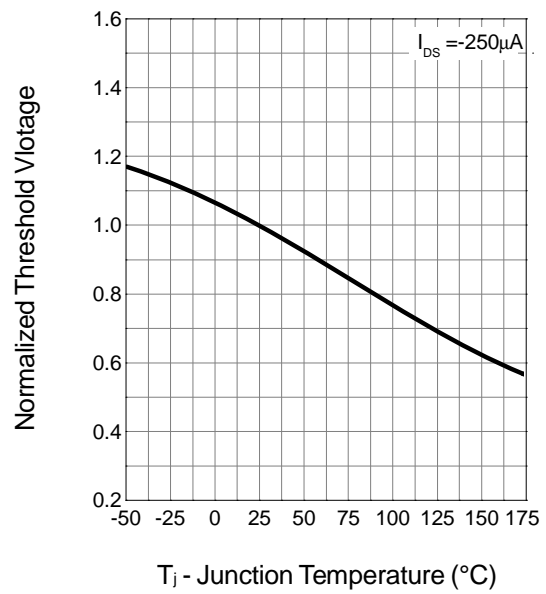
**Drain-Source On Resistance**



**Drain-Source On Resistance**

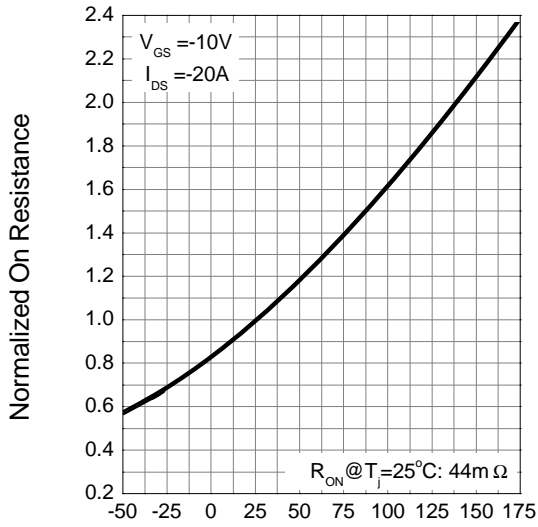


**Gate Threshold Voltage**



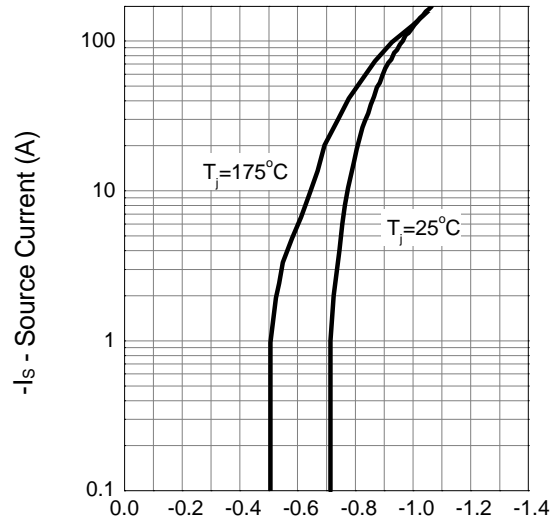
**Typical Characteristics**

**Drain-Source On Resistance**



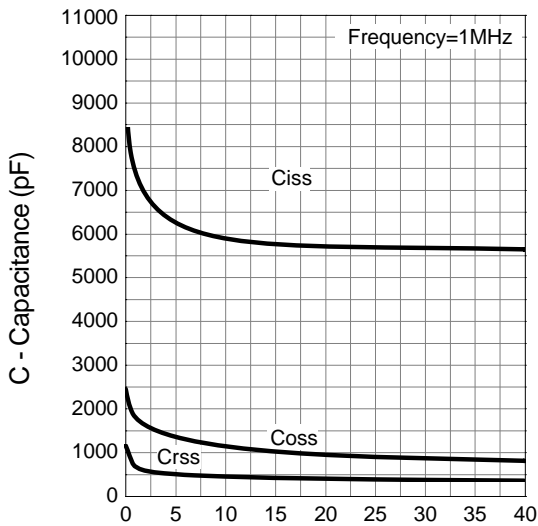
$T_j$  - Junction Temperature ( $^{\circ}C$ )

**Source-Drain Diode Forward**



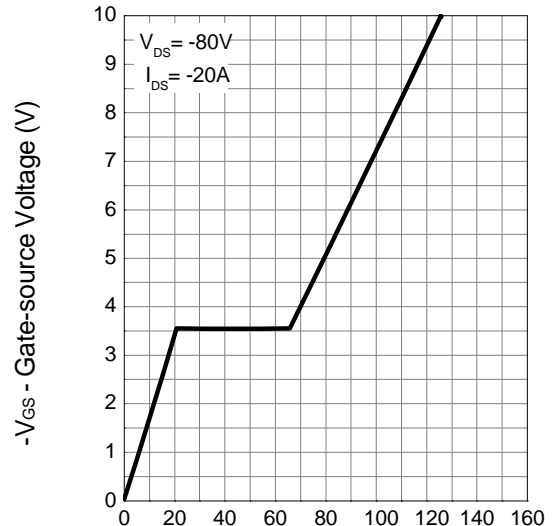
$-V_{SD}$  - Source-Drain Voltage (V)

**Capacitance**



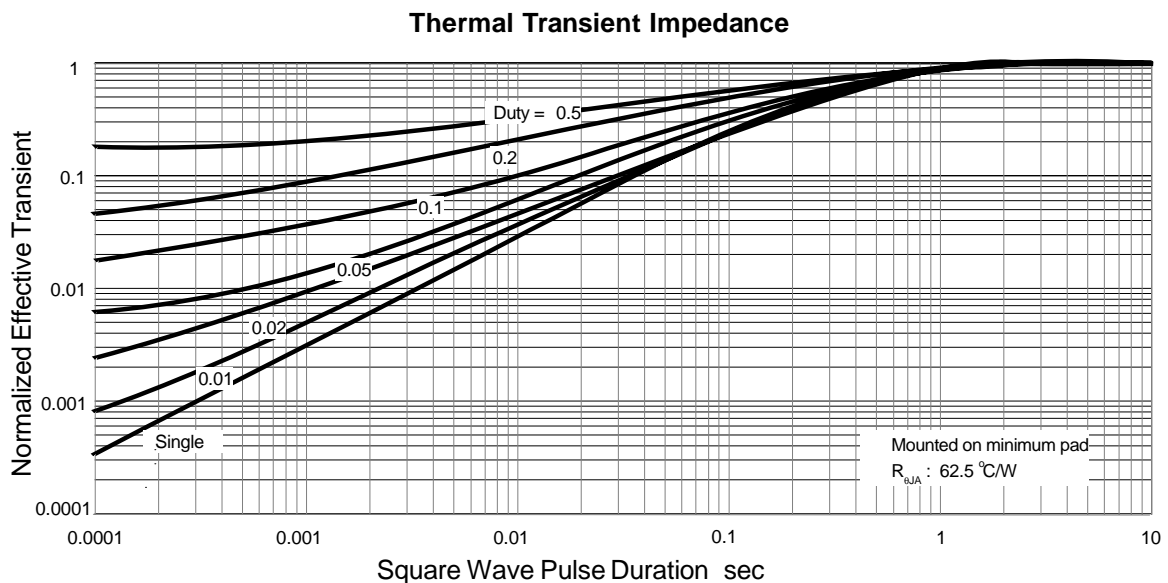
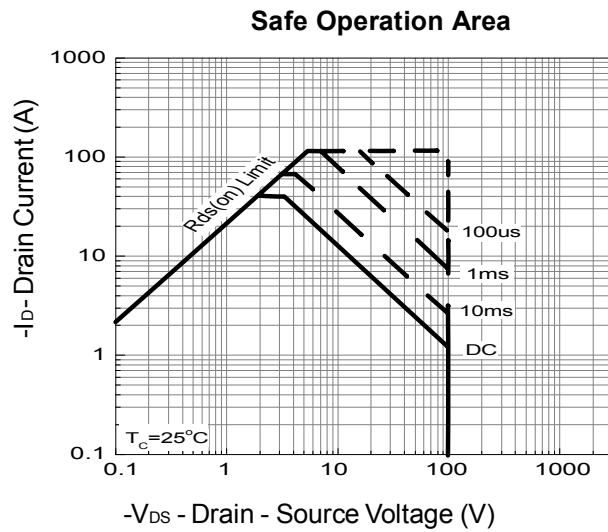
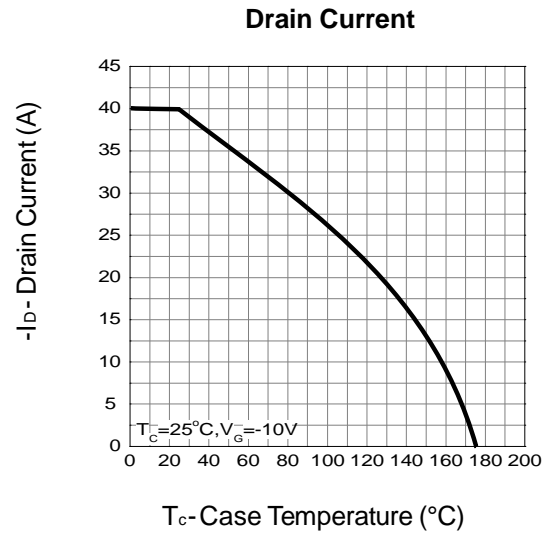
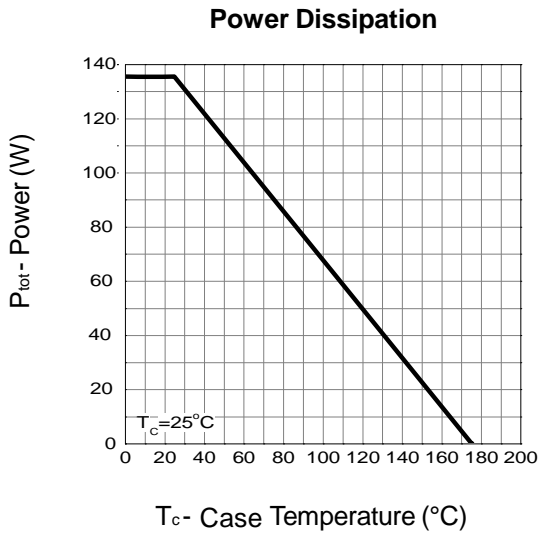
$-V_{DS}$  - Drain - Source Voltage (V)

**Gate Charge**



$Q_G$  - Gate Charge (nC)

**Typical Characteristics**





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